

Description

SEMICONDUCTOR DEVICE WITH A NEGATIVE VOLTAGE REGULATOR

BACKGROUND OF INVENTION

[0001] 1. Field of the Invention

[0002] The present invention relates to a semiconductor device with a negative voltage regulator, and more particularly, to a semiconductor device with a negative voltage regulator utilizing triple-well NMOS transistors.

[0003] 2. Description of the Prior Art

[0004] There are a lot of applications that utilize regulators for tasks of regulating voltages. Many designs and patents of regulators have been developed for improving the performance of regulator circuits. One of the examples is US Patent No. 6,600,692, *Semiconductor Device with a Voltage Regulator* to Tanzawa, which is included herein by reference.

[0005] Many applications require circuits that can boost up an in-

put power supply DC voltage to a higher DC voltage used for specialized operations. The reason for the voltage boost up is that often only standardized power supply voltages are available for supplying power to electronic circuits. However, sometimes there are situations where a circuit needs a higher voltage than one available from the associated power supply. In addition, other circuits even require a negative voltage though only positive voltages from a power supply are available. One example of such a circuit is an electrical erasable programmable read only memory (EEPROM), typically termed in the art as "flash memory". A flash memory may require a negative voltage to perform erase operations. However, there are few achievements in regulating negative voltages. Techniques for regulating positive voltages, such as illustrated in US6,600,692 are not applicable to regulating negative voltages. In general, a negative pump is often utilized to generate a negative voltage. Please refer to Fig. 1. Fig. 1 is a block diagram of a prior art negative voltage generator 100. The negative voltage generator 100 includes an oscillator 110 and a negative pump 120. The oscillator 110 outputs its output to the negative pump 120, and then a negative voltage V_{OUT1} is output from the negative pump

120. Please refer to Fig. 2. Fig. 2 is a block diagram of a prior art negative voltage regulator 200. The negative voltage generating circuit part includes an oscillator 210 and a negative pump 220 the same as the circuit in Fig. 1. The negative voltage regulating circuit part includes an AND gate 230, a voltage potential divider 240 and a comparator 250. V_{ref21} and V_{ref22} are two reference voltages. R21 and R22 are two voltage dividing resistors. Compared to the unregulated voltage V_{OUT1} in Fig. 1, the voltage potential divider 240 divides the output voltage of the negative pump 220, $V_{\text{OUT2'}}$, and the reference voltage $V_{\text{ref21'}}$, and then inputs the voltage V_{FEBK2} generated in the voltage division into the comparator 250 to be compared with the reference voltage V_{ref22} . The output of the comparator 250 and the output of the oscillator 210 are input to the AND gate 230, and the output of the AND gate 230 is then input to the negative pump 220. Thereby a regulation loop is formed, and the voltage V_{OUT2} is a regulated negative output voltage.

[0006] For circuits that require high precision, the conventional negative voltage regulator 200 illustrated in Fig. 2 is not ideal. The operation of the conventional negative voltage regulator 200 illustrated in Fig. 2 is described as below.

When the potential of the voltage V_{OUT2} is lower than a predetermined potential, the feedback voltage V_{FEBK} will be pulled down and the output of the comparator 250 is made digital 0 (low potential). The output of the AND gate 230 is made digital 0, hence the negative pump 220 stops charging along with the oscillator 210 and pulls up the potential of the voltage V_{OUT2} . Contrarily, when the potential of the voltage V_{OUT2} is higher than the predetermined potential, the feedback voltage V_{FEBK} will be pulled up and the output of the comparator 250 is made digital 1 (high potential). Therefore the negative pump 220 charges along with the oscillator 210 and then decreases the potential of the voltage V_{OUT2} . The regulation as described above is limited by the comparison range of the comparator 250 and the AND gate 230, and is similar to digital feedback regulation. The potential of the regulated voltage V_{OUT2} still suffers significant ripple. In addition, the performance of the conventional negative voltage regulator 200 does not sufficiently meet the requirements of circuits that need to utilize negative voltages.

SUMMARY OF INVENTION

[0007] It is therefore a primary objective of the claimed invention to provide a semiconductor device with a negative voltage

regulator.

[0008] Briefly described, the claimed invention discloses a semiconductor device with a negative voltage regulator. The semiconductor device includes a negative voltage regulator capable of regulating a negative input voltage and outputting a negative output voltage at an output node. The negative voltage regulator comprises a driver for adjusting the negative output voltage, a first operational amplifier capable of outputting a driving voltage for controlling a current of a first transistor included in the driver according to a feedback voltage and a reference voltage, a second operational amplifier capable of outputting a driving voltage for controlling a current of a second transistor included in the driver according to a reference voltage and the feedback voltage, a current source circuit comprising two triple-well NMOS transistors and capable of providing the driver a current, and a voltage potential divider capable of generating the feedback voltage by dividing potentials of a voltage source and the negative output voltage and outputting the feedback voltage to the first operational amplifier and the second operational amplifier for adjusting the current on the first transistor and the current on the second transistor and thereby regulating the

negative output voltage.

[0009] It is an advantage of the present invention that utilization of triple-well NMOS transistors enables the biasing at a negative voltage and hence achieves negative voltage regulation. The problem of excessive ripples of the negative output voltage in the conventional negative regulator is reduced and the requirements of circuits that utilize negative voltages are met.

[0010] These and other objectives of the present invention will no doubt become obvious to those of ordinary skill in the art after reading the following detailed description of the preferred embodiments that are illustrated in the various figures and drawings.

BRIEF DESCRIPTION OF DRAWINGS

[0011] Fig. 1 is a block diagram of a prior art negative voltage generator.

[0012] Fig. 2 is a block diagram of a prior art negative voltage regulator.

[0013] Fig. 3 is a block diagram of the present invention semiconductor device with a negative voltage regulator.

DETAILED DESCRIPTION

[0014] Please refer to Fig. 3. Fig. 3 is a block diagram of the

present invention semiconductor device 300 with a negative voltage regulator 30. The negative voltage regulator 30 includes a voltage source regulator 310, a current source circuit 320, a voltage potential divider 340, a driver 350 and two operational amplifiers 361 and 362. An unregulated negative input voltage V_{IN3} is input to the negative voltage regulator 30 at an input node N_{IN} . The negative voltage regulator 30 is capable of regulating the negative input voltage V_{IN3} and outputting a regulated negative output voltage V_{OUT3} at an output node N_{OUT} . 330 is a reference voltage generator, such as a band gap circuit, included in the present semiconductor device 300. The reference voltage generator 330 is capable of generating reference voltages utilized in the circuits included in the device 300. Reference voltages V_{ref31} and V_{ref32} are two examples of the reference voltages generated by the reference voltage generator 330.

[0015] The voltage regulator 310 is utilized to regulate a voltage source V_{DD} . The voltage regulator 310 includes a PMOS transistor p3 and an operational amplifier 363. The source of the PMOS transistor p3 is electrically connected to the high level voltage source of the circuit, that is, V_{DD} , and the drain of the PMOS transistor p3 is electrically con-

nected to a node N_S . As shown in Fig. 3, the two input ends of the operational amplifier 363 are separately electrically connected to the drain of the PMOS transistor p3 and a reference voltage V_{ref31} provided by the reference voltage generator 330, and the output end of the operational amplifier 363 is electrically connected to the gate of the PMOS transistor p3. The voltage regulator 310 is capable of providing a stable voltage source V_S independent of the unstable voltage source V_{DD} at the node N_S by fixing the voltage potential of the drain of the PMOS transistor p3 to the potential of the reference voltage V_{ref31} . The current source circuit 320 includes two triple-well NMOS transistors n1 and n2. The current on the NMOS transistor n1 is proportional to the current on the NMOS transistor n2. The sources of the NMOS transistors n1 and n2 are electrically connected to the input node N_{IN} . Since the NMOS transistors n1 and n2 are triple-well NMOS transistors, the voltage potentials at their drains and sources can be negative. The negative input voltage V_{IN3} is input to the negative voltage regulator 30 at the sources of the NMOS transistor n1 and n2. The voltage potential divider 340 is utilized to divide the negative output voltage V_{OUT3} and feedback the division to the present voltage regulator 30.

There are many embodiments of the voltage potential divider. The voltage potential divider 340 illustrated in Fig. 3 is the simplest one. As shown in Fig. 3, the voltage potential divider 340 includes two dividing resistors R31 and R32. The two ends of the voltage potential divider 340 are electrically connected to the output node N_{OUT} of the negative voltage regulator 30 and the node N_S for dividing the voltage V_S and the negative output voltage V_{OUT3} and feeding back the division to the present voltage regulator 30. The driver 350 includes two PMOS transistors p1 and p2. The sources of the transistors p1 and p2 are electrically connected to the node N_S receiving the stable voltage source V_S . The gates of the transistors p1 and p2 are electrically connected to the output ends of the operational amplifiers 361 and 362 respectively, therefore the output voltages of the operational amplifiers 361 and 362 control the current I_1 that flows through the transistor p1 and the current I_2 that flows through the transistor p2 respectively. Each of the two operational amplifiers 361 and 362 receives the reference voltage V_{ref32} generated by the reference voltage generator 330 at one input end, and electrically connects to the node N_{FEBK3} by the other input end receiving the feedback voltage V_{FEBK3} .

[0016] As illustrated in Fig. 3 and the described above, the operation of the present negative voltage regulator 30 can be presented as follows. First, assume that the voltage regulator 310 and the voltage potential divider 340 are well designed and the values of the reference voltages V_{ref31} and V_{ref32} are well chosen for coordination. When the negative output voltage V_{OUT3} is higher than a target potential, the feedback voltage V_{FEBK3} increases and exceeds the reference voltage V_{ref32} accordingly. Thereby the output voltage of the operational amplifier 361 is at high level and the output voltage of the operational amplifier 362 is at low level, which leads to a decreasing of the current I_1 and an increasing of the current I_2 . However, the currents on the transistor n1 and n2 are proportional. If the current I_1 decreases and the current I_2 increases, there must be some current flowing from the node N_{OUT} to the transistor n1 to complement the current I_1 . This current will pull down the feedback voltage V_{FEBK3} and the negative output voltage V_{OUT3} , that is, adjust the negative output voltage V_{OUT3} to the target potential level. On the contrary, if the negative output voltage V_{OUT3} is lower than the target potential, the feedback voltage V_{FEBK3} decreases and becomes lower than the reference voltage V_{ref32}

accordingly. Thereby the output voltage of the operational amplifier 361 is at low level and the output voltage of the operational amplifier 362 is at high level, which leads to an increasing of the current I_1 and a decreasing of the current I_2 . Similarly, if the current I_1 increases and the current I_2 decreases, there must be some part of current I_1 flowing from the node N_{OUT} to the voltage potential divider 340. This current will pull up the feedback voltage V_{FEBK3} and the negative output voltage V_{OUT3} , that is, adjust the negative output voltage V_{OUT3} to the target potential level.

[0017] The present invention feeds back the division of the negative output voltage V_{OUT3} to the negative voltage regulator 30 for controlling the currents I_1 and I_2 through the transistors p1 and p2 included in the driver 350, and adjusts the potential of the negative output voltage V_{OUT3} to a target potential level by the variation of the currents I_1 and I_2 . One of the characteristics of the present invention is the utilization of the two triple-well NMOS transistors. As it is known, it is better to bias the source and the base of a transistor at the same voltage potential. The triple-well NMOS transistors utilized in the present invention enables the sources and the drains of the transistors n1 and n2 to be connected to negative voltages. Therefore the

sources of the transistors n1 and n2 can be the input node of the present invention negative voltage regulator, and the drain of the transistor n1 can be the output node of the present invention negative voltage regulator. Consequently the negative voltage regulation is implemented.

[0018] The circuit illustrated in Fig. 3 is one of the embodiments of the present semiconductor device with a negative voltage regulator. In implementation, the divider 340 may connect to the output node N_{OUT} and a reference voltage V_{ref33} other than V_S , and the elements comprised in the divider 340 and the structure of the divider 340 may be different with suitable design. The voltage regulator 310 may be omitted or be replaced by another band gap circuit. The structure of the driver 350 shown in Fig. 3 is the simplest example. Other circuits with different structures but the same function may replace the driver 350 in the present invention.

[0019] In summary, the present invention takes advantage of the property of the triple-well NMOS transistors and provides a precise and effective negative voltage regulator. The output regulated negative voltage of the present invention is stable and thereby improves the performance of the circuits that need to utilize negative voltage. It has been

shown by experiment that, if the negative input voltage is -7 V with noise of 200 mV, the negative output voltage regulated by the present negative voltage regulator will be -7V with noise of less than 50 mV. In contrast to the conventional negative voltage regulator, the claimed negative voltage regulator provides negative voltage regulation with high performance and supports the operation of flash memory cards.

[0020] Those skilled in the art will readily observe that numerous modifications and alterations of the device may be made while retaining the teachings of the invention. Accordingly, the above disclosure should be construed as limited only by the metes and bounds of the appended claims.